

AMENDMENT TO THE CLAIMS

1. (Currently amended) A method of manufacturing a memory cell comprising an electrically conductive word line, an electrically conductive bit line, an electrical charge storage structure, a transistor structure, and a bit line contact, said method comprising the steps of:

forming said charge storage structure so as to be conductively coupled to said bit line via said transistor structure and said bit line contact;

forming said transistor structure so as to be conductively coupled to said word line;

forming said bit line contact by forming a conductively doped polysilicon plug within a contact hole bounded by insulating side walls; and

forming said doped polysilicon plug so as to define ~~a substantially convex~~ an upwardly curved upper plug surface profile in contact with said bit line, wherein said upwardly curved upper plug surface profile extends from an uppermost extent of one insulating side wall to an uppermost extent of an opposing insulating side wall such that said upwardly curved upper plug surface profile is at least partially above the opposing insulating side walls.

2. (Previously presented) A method of manufacturing a memory cell as claimed in claim 1 wherein said insulating side walls are formed so as to comprise a first pair of opposing insulating side walls along a first dimension and a second pair of opposing insulating side walls along a second dimension.

3. (Original) A method of manufacturing a memory cell as claimed in claim 2 wherein said first pair of opposing insulating side walls are formed so as to comprise respective layers of insulating spacer material formed over a conductive line.

4. (Original) A method of manufacturing a memory cell as claimed in claim 2 wherein said second pair of opposing insulating side walls are formed so as to comprise respective layers of insulating material formed between respective contact holes.

5. (Original) A method of manufacturing a memory cell as claimed in claim 1 wherein said contact hole is filled with said polysilicon plug to an uppermost extent of said insulating side walls.

6-18. (Canceled)